

Substitute form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet A1 of A3

Complete if Known

Application Number	10/758,871
Filing Date	January 16, 2004
First Named Inventor	Sheppard
Group Art Unit	2611 2812
Examiner Name	Tom Thomas Geyer, S.
Attorney Docket Number	5308-291

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Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
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Examiner Signature

SBG

Date Considered


12-8-05

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Sheet	A2	of	A3	Attorney Docket Number	5308-291

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Examiner Signature		Date Considered	1-12-06
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